SLUS339A – JUNE 1993 – REVISED MAY 2001

DUAL SCHOTTKY DIODE BRIDGE

FEATURES

- **Monolithic Eight-Diode Array**
- **Exceptional Efficiency**
- **Low Forward Voltage**
- **Fast Recovery Time**
- **High Peak Current**
- **Small Size**

DESCRIPTION

This eight-diode array is designed for high-current, low duty-cycle applications typical of flyback voltage clamping for inductive loads. The dual bridge connection makes this device particularly applicable to bipolar driven stepper motors.

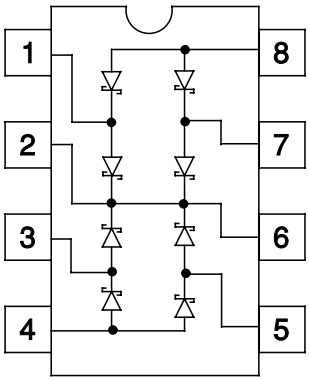
The use of Schottky diode technology features high efficiency through lowered forward voltage drop and decreased reverse recovery time.

This single monolithic chip is fabricated in both hermetic CERDIP and copper-leaded plastic packages. The UC1610 in ceramic is designed for –55°C to 125°C environments but with reduced peak current capability. The UC2610 in plastic and ceramic is designed for –25°C to 125°C environments also with reduced peak current capability; while the UC3610 in plastic has higher current rating over a 0°C to 70°C temperature range.

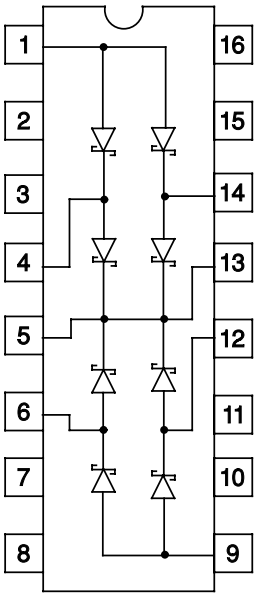
AVAILABLE OPTIONS

$T_A = T_J$	Packaged Devices		
	SOIC Wide (DW)	DIL (J)	DIL (N)
–55°C to 125°C	UC1610DW	UC1610J	UC1610N
–25°C to 125°C	UC2610DW	UC2610J	UC2610N
0°C to 70°C	UC3610DW	UC3610J	UC3610N

N OR J PACKAGE
TOP VIEW



DW PACKAGE
TOP VIEW



absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Peak inverse voltage (per diode) . . . . . 50 V
Peak forward current
UC1611 . . . . . 1 A
UC2610 . . . . . 1 A
UC3611 . . . . . 3 A
Power dissipation at T_A = 70°C . . . . . 1 W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C
Lead temperature (soldering, 10 seconds) . . . . . 300°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
‡ Consult packaging section of databook for thermal limitations and considerations of package.

electrical characteristics, all specifications apply to each individual diode, T_J = 25°C, $T_A = T_J$, (except as noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Forward voltage drop	I_F = 100 mA	0.35	0.5	0.7	V
	I_F = 1 A	0.8	1.0	1.3	V
Leakage current	V_R = 40 V		0.01	0.1	mA
	V_R = 40 V, T_J = 100°C		0.1	1.0	mA
Reverse recovery	0.5 A forward to 0.5 A reverse		15		ns
Forward recovery	1 A forward to 1.1 V recovery		30		ns
Junction capacitance	V_R = 5 V		70		pF

NOTE: At forward currents of greater than 1.0 A, a parasitic current of approximately 10 mA may be collected by adjacent diodes.

APPLICATION INFORMATION

REVERSE CURRENT
vs
VOLTAGE

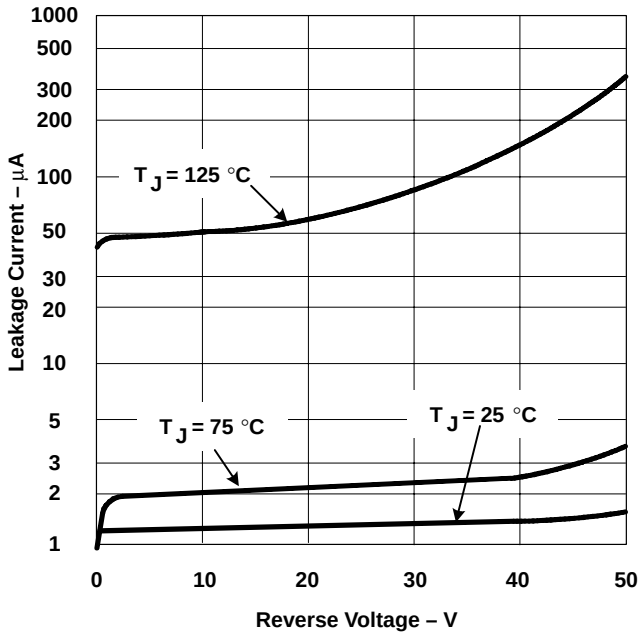


Figure 1

FORWARD CURRENT
vs
VOLTAGE

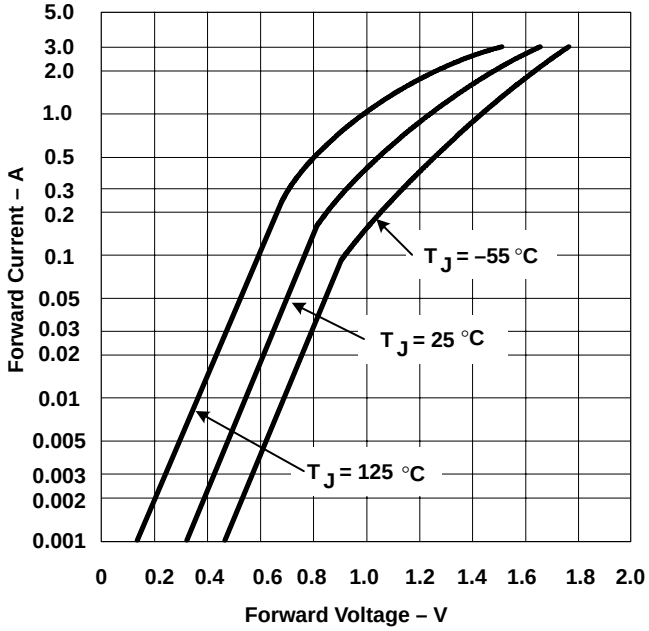


Figure 2

REVERSE RECOVERY CHARACTERISTICS

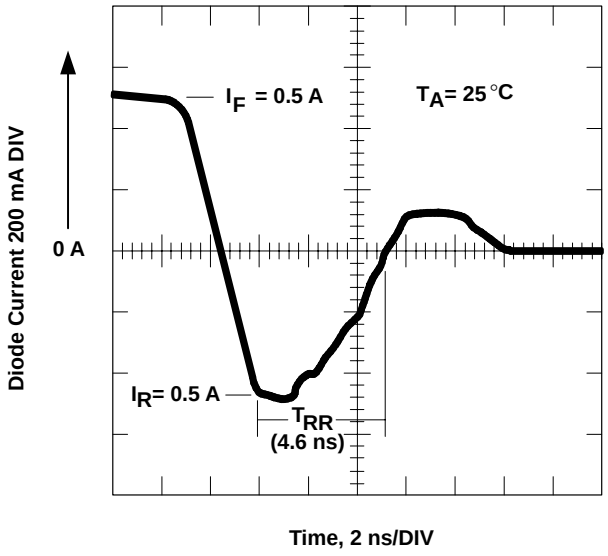


Figure 3

FORWARD RECOVERY CHARACTERISTICS

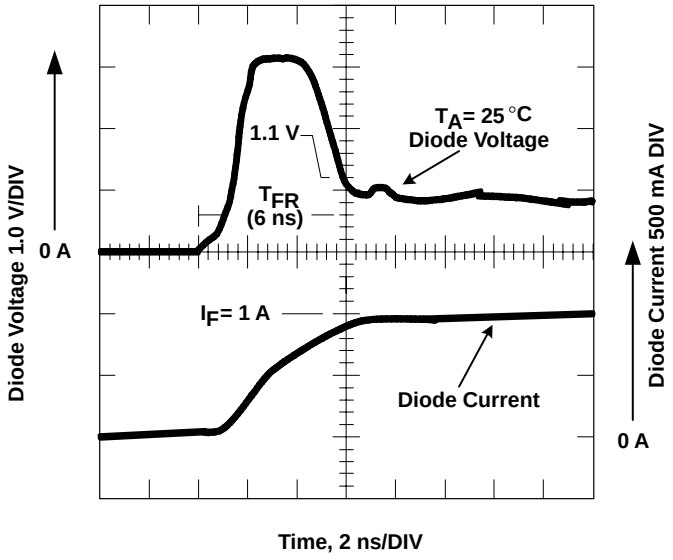


Figure 4

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgment, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Customers are responsible for their applications using TI components.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, license, warranty or endorsement thereof.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations and notices. Representation or reproduction of this information with alteration voids all warranties provided for an associated TI product or service, is an unfair and deceptive business practice, and TI is not responsible nor liable for any such use.

Resale of TI's products or services with *statements different from or beyond the parameters* stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service, is an unfair and deceptive business practice, and TI is not responsible nor liable for any such use.

Also see: Standard Terms and Conditions of Sale for Semiconductor Products. www.ti.com/sc/docs/stdterms.htm

Mailing Address:

Texas Instruments
Post Office Box 655303
Dallas, Texas 75265